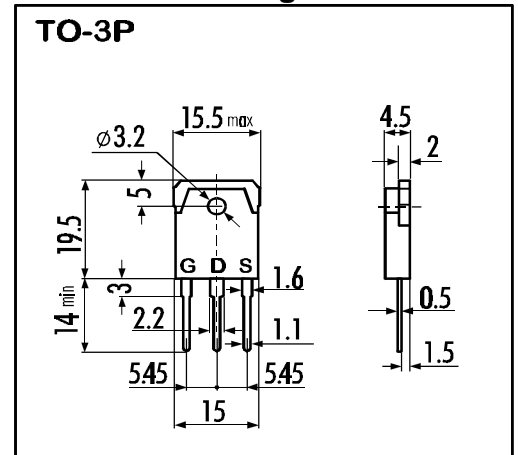


> Features

- High Speed Switching
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Voltage
- $V_{GS} = \pm 30V$ Guarantee
- Repetitive Avalanche Rated

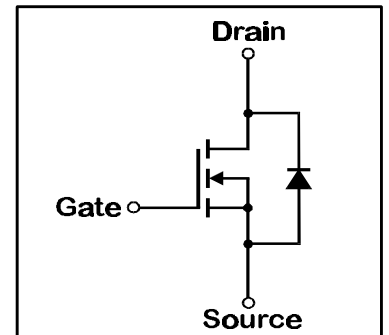
> Applications

- Switching Regulators
- UPS
- DC-DC converters
- General Purpose Power Amplifier

> Outline Drawing

> Maximum Ratings and Characteristics

 - Absolute Maximum Ratings ($T_C=25^\circ\text{C}$), unless otherwise specified

| Item | Symbol | Rating | Unit |
|--|---------------|------------|------------------|
| Drain-Source-Voltage | V_{DS} | 900 | V |
| Continous Drain Current | I_D | 3,5 | A |
| Pulsed Drain Current | $I_{D(puls)}$ | 14 | A |
| Gate-Source-Voltage | V_{GS} | ± 30 | V |
| Repetitive or Non-Repetitive ($T_{ch} \leq 150^\circ\text{C}$) | I_{AR} | 3,5 | A |
| Avalanche Energy | E_{AS} | 364 | mJ |
| Max. Power Dissipation | P_D | 100 | W |
| Operating and Storage Temperature Range | T_{ch} | 150 | $^\circ\text{C}$ |
| | T_{stg} | -55 ~ +150 | $^\circ\text{C}$ |

> Equivalent Circuit

 - Electrical Characteristics ($T_C=25^\circ\text{C}$), unless otherwise specified

| Item | Symbol | Test conditions | Min. | Typ. | Max. | Unit |
|--|---------------|--|------|------|------|---------------|
| Drain-Source Breakdown-Voltage | $V_{(BR)DSS}$ | $I_D=1\text{mA}$ $V_{GS}=0\text{V}$ | 900 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $I_D=1\text{mA}$ $V_{DS}=V_{GS}$ | 3,5 | 4,0 | 4,5 | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=900\text{V}$ $T_{ch}=25^\circ\text{C}$ | | 10 | 500 | μA |
| | | $V_{GS}=0\text{V}$ $T_{ch}=125^\circ\text{C}$ | | 0,2 | 1,0 | mA |
| Gate Source Leakage Current | I_{GSS} | $V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$ | | 10 | 100 | nA |
| Drain Source On-State Resistance | $R_{DS(on)}$ | $I_D=2\text{A}$ $V_{GS}=10\text{V}$ | | 4 | 5,5 | Ω |
| Forward Transconductance | g_{fs} | $I_D=2\text{A}$ $V_{DS}=25\text{V}$ | | 2 | | S |
| Input Capacitance | C_{iss} | $V_{DS}=25\text{V}$ | | 450 | | pF |
| Output Capacitance | C_{oss} | $V_{GS}=0\text{V}$ | | 75 | | pF |
| Reverse Transfer Capacitance | C_{rss} | $f=1\text{MHz}$ | | 40 | | pF |
| Turn-On-Time t_{on} ($t_{on}=t_{d(on)}+t_r$) | $t_{d(on)}$ | $V_{CC}=600\text{V}$ | | 20 | | ns |
| | | $I_D=7\text{A}$ | | 40 | | ns |
| Turn-Off-Time t_{off} ($t_{off}=t_{d(off)}+t_f$) | $t_{d(off)}$ | $V_{GS}=10\text{V}$ | | 50 | | ns |
| | | $R_{GS}=10\ \Omega$ | | 25 | | ns |
| Avalanche Capability | I_{AV} | $L=100\ \mu\text{H}$ $T_{ch}=25^\circ\text{C}$ | 3,5 | | | A |
| Diode Forward On-Voltage | V_{SD} | $I_F=2 \times I_{DR}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$ | | 1,0 | | V |
| Reverse Recovery Time | t_{rr} | $I_F=I_{DR}$ $V_{GS}=0\text{V}$ | | 500 | | ns |
| Reverse Recovery Charge | Q_{rr} | $-dI_F/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$ | | 3 | | μC |

- Thermal Characteristics

| Item | Symbol | Test conditions | Min. | Typ. | Max. | Unit |
|--------------------|----------------|-----------------|------|------|------|---------------------------|
| Thermal Resistance | $R_{th(ch-a)}$ | channel to air | | | 35 | $^\circ\text{C}/\text{W}$ |
| | $R_{th(ch-c)}$ | channel to case | | | 1,25 | $^\circ\text{C}/\text{W}$ |

| | | | |
|-------------------|------|------|------|
| N-channel MOS-FET | | | |
| 900V | 5,5Ω | 3,5A | 100W |

2SK2770-01

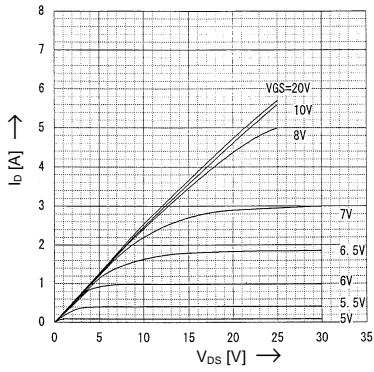
FAP-IIS Series



> Characteristics

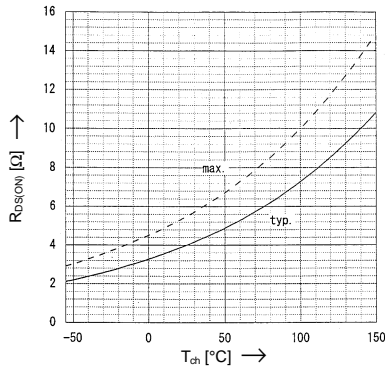
Typical Output Characteristics

$I_D=f(V_{DS})$; 80μs pulse test; $T_C=25^\circ\text{C}$



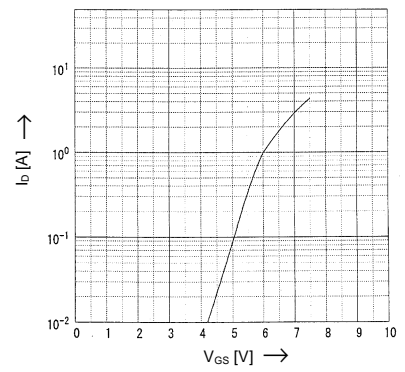
Drain-Source On-State Resistance vs. T_{ch}

$R_{DS(on)}=f(T_{ch})$; $I_D=2\text{A}$; $V_{GS}=10\text{V}$



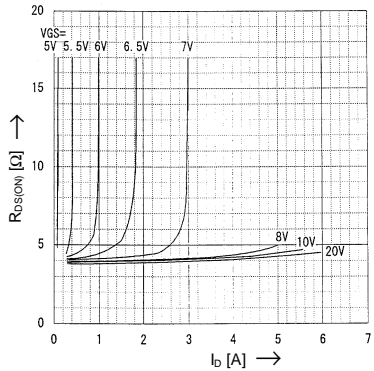
Typical Transfer Characteristics

$I_D=f(V_{GS})$; 80μs pulse test; $V_{DS}=25\text{V}$; $T_{ch}=25^\circ\text{C}$



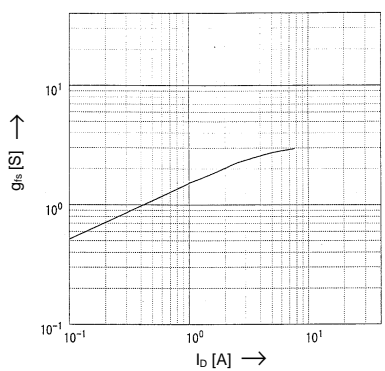
Typical Drain-Source On-State-Resistance vs. I_D

$R_{DS(on)}=f(I_D)$; 80μs pulse test; $T_C=25^\circ\text{C}$



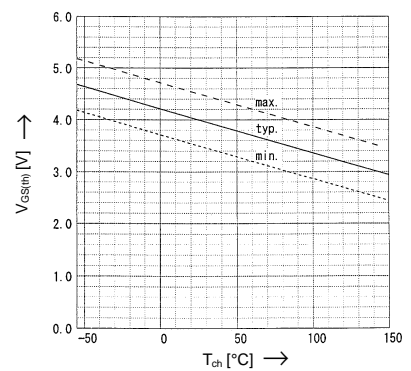
Typical Forward Transconductance vs. I_D

$g_{fs}=f(I_D)$; 80μs pulse test; $V_{DS}=25\text{V}$; $T_{ch}=25^\circ\text{C}$



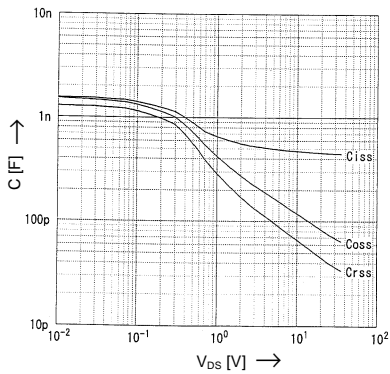
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)}=f(T_{ch})$; $I_D=1\text{mA}$; $V_{DS}=V_{GS}$



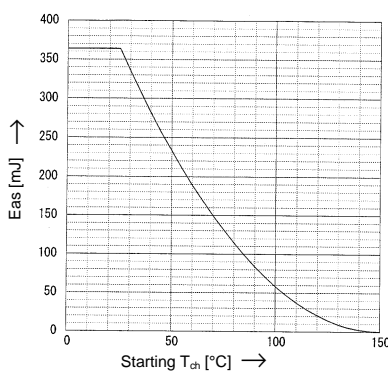
Typical Capacitances vs. V_{DS}

$C=f(V_{DS})$; $V_{GS}=0\text{V}$; $f=1\text{MHz}$



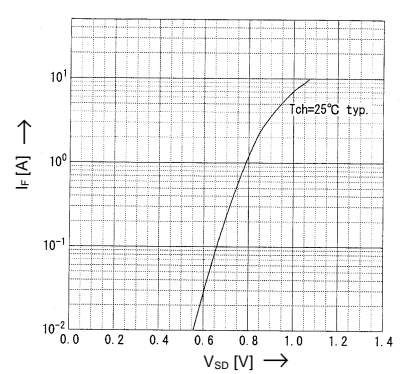
Avalanche Energy Derating

$E_{as}=f(\text{starting } T_{ch})$; $V_{CC}=90\text{V}$; $I_{AV}=3,5\text{A}$



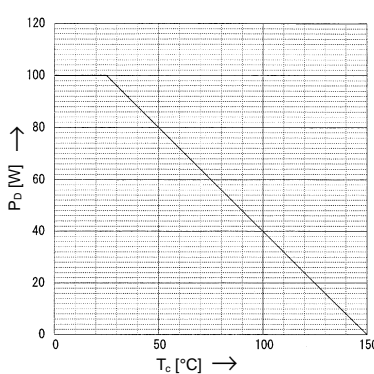
Forward Characteristics of Reverse Diode

$I_F=f(V_{SD})$; 80μs pulse test; $V_{GS}=0\text{V}$



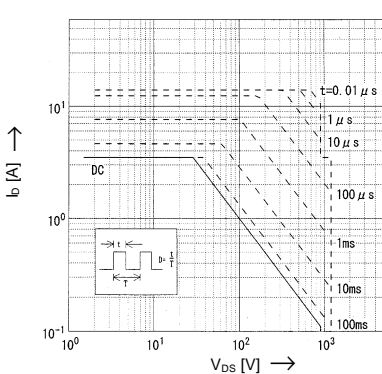
Allowable Power Dissipation vs. T_C

$P_D=f(T_C)$



Safe Operation Area

$I_D=f(V_{DS})$; $D=0,01$; $T_C=25^\circ\text{C}$



Transient Thermal impedance

$Z_{th(ch-e)}=f(t)$ parameter: $D=t/T$

